

2MBI400VD-120-50

IGBT Modules

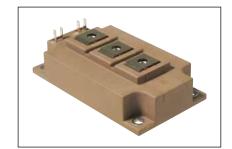
IGBT MODULE (V series) 1200V / 400A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

■ Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Collector-Emitte	er voltage	Vces				V	
Gate-Emitter vo	Gate-Emitter voltage				±20	V	
_	urrent	Ic	Continuous	Tc=100°C	400		
#				Tc=25°C	520		
S Collector curre		Ic pulse	1ms		800		
드		-lc			400		
		-lc pulse	1ms	1ms			
Collector power dissipation		Pc	1 device	1 device		W	
Junction temperature		Tj			175		
Operating junction temperature (under switching conditions)		T _{jop}		150		°C	
Case temperature		Tc			125	C	
Storage temperature		Tstg			-40 ~ +125		
Isolation voltage between terminal and copper base (*1)		Viso	AC : 1min.		2500	VAC	
Sarau taraua	Mounting (*2)				6.0	NI	
Screw torque	Terminals (*3)]-			5.0	N m	

Note *1: All terminals should be connected together during the test. Note *2: Recommendable Value : 3.0-6.0 Nm (M5 or M6) Note *3: Recommendable Value : 2.5-5.0 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

ems	Cumbala	Conditions		Characteristics			Units
ans	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	2.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA
Gate-Emitter threshold voltage VGE (th) VCE = 20V, Ic		V _{CE} = 20V, I _C = 400mA	= 400mA		6.5	7.0	V
	V	V _{GE} = 15V Ic = 400A	Tj=25°C	-	1.95	2.40	V
	V _{CE (sat)} (terminal)		Tj=125°C	-	2.25	-	
Collector Emitter acturation valtage	(terminar)		Tj=150°C		2.30		
Collector-Emitter saturation voltage	V _{CE (sat)} (chip)		Tj=25°C	-	1.75	2.15	
			Tj=125°C	-	2.05	-	
			Tj=150°C		2.00		
Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	36.4	-	nF
Input capacitance	ton	Vcc = 600V		-	0.60	-	μs
Turn-on time	tr	Ic = 400A	-	0.20	-		
	tr (i)	V _{GE} = ±15V	-	0.05	-		
Turn off time	toff	$R_G = 1\Omega$		-	0.80	-	
Turn-off time	tf	∏Tj = 150°C	-	0.08	-		
	V	V _{GE} = 0V I _F = 400A	Tj=25°C	-	1.85	2.30	V
	V _F		Tj=125°C	-	2.00	-	
Famuerd on veltage	(terminal)		Tj=150°C		1.95		
Forward on voltage	V		Tj=25°C	-	1.70	2.15	
	V _F		Tj=125°C	-	1.85	-	
	(chip)		Tj=150°C		1.80		
Reverse recovery time trr I _F = 400A			<u> </u>	-	0.15	-	μs

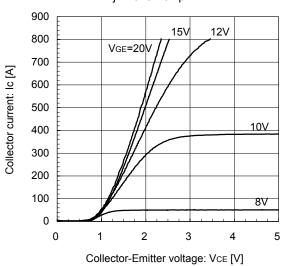
Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units		
items	Symbols	Conditions	min.	typ.	max.	Units		
Thermal register on (1 device)	Rth(j-c)	IGBT	-	-	0.045	°C/W		
Thermal resistance (1device)		FWD	-	-	0.077			
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.013	_	1		

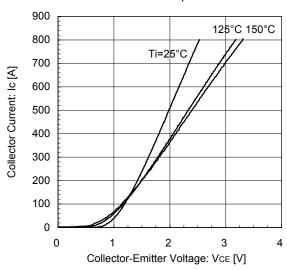
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

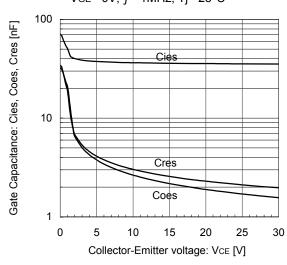
Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



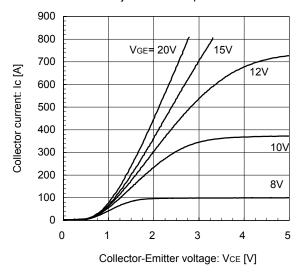
Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



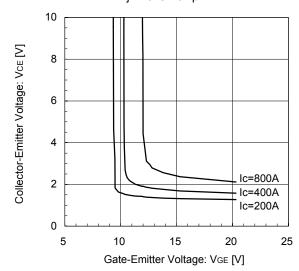
Gate Capacitance vs. Collector-Emitter Voltage . VGE= 0V, *f*= 1MHz, Tj= 25°C



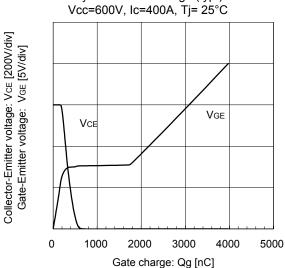
Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip



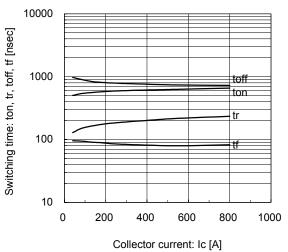
Collector-Emitter voltage vs. Gate-Emitter voltage Tj= 25°C / chip



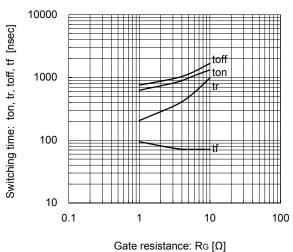
Dynamic Gate Charge (typ.)



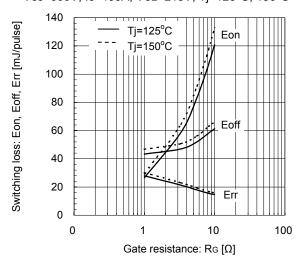
Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg= 1Ω , Tj= 125° C



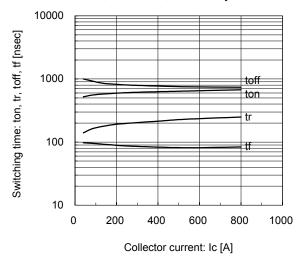
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=400A, $VgE=\pm15V$, $Tj=125^{\circ}C$



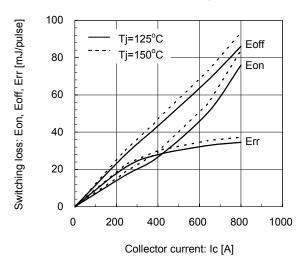
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=400A, VgE=±15V, Tj=125°C, 150°C



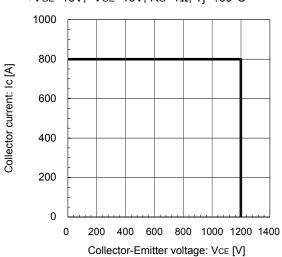
Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg= 1Ω , Tj=150°C

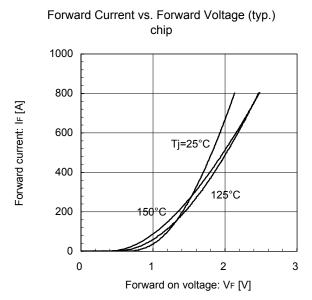


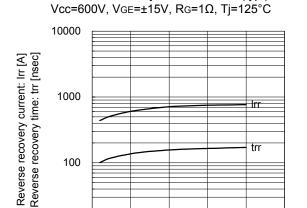
Switching loss vs. Collector current (typ.) Vcc=600V, VgE=±15V, Rg=1Ω, Tj=125°C, 150°C



Reverse bias safe operating area (max.) +VGE=15V, -VGE=15V, RG=1 Ω , Tj=150°C

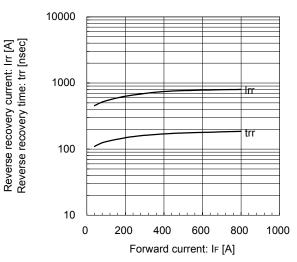






Reverse Recovery Characteristics (typ.)

Reverse Recovery Characteristics (typ.) Vcc=600V, VgE= \pm 15V, Rg= 1Ω , Tj= 150° C



Transient Thermal Resistance (max.)

400

600

Forward current: IF [A]

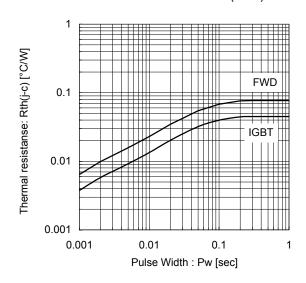
800

1000

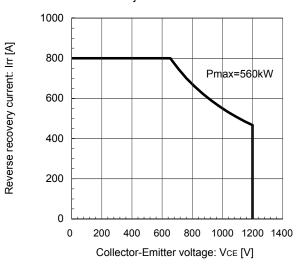
10

0

200

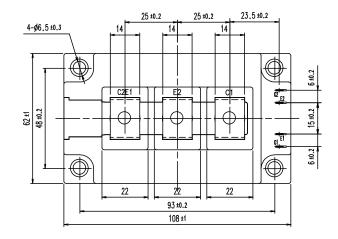


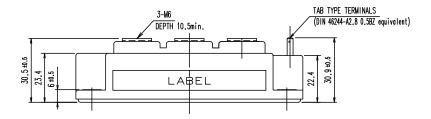
FWD safe operating area (max.) Tj=150°C



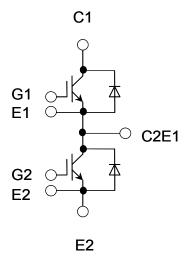
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■ Outline Drawings, mm





■ Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

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- Machine tools
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- Electrical home appliances Personal e
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